



## UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE  
 United States Patent and Trademark Office  
 Address: COMMISSIONER FOR PATENTS  
 P.O. Box 1450  
 Alexandria, Virginia 22313-1450  
 www.uspto.gov



Bib Data Sheet

CONFIRMATION NO. 3843

SERIAL NUMBER 10/749,134	FILING DATE 12/30/2003  RULE	CLASS 257	GROUP ART UNIT 2826	ATTORNEY DOCKET NO. 02CT20753422
-----------------------------	---------------------------------------	--------------	------------------------	--

## APPLICANTS

Angelo Magri', Belpasso, ITALY;

Ferruccio Frisina, Sant'Agata Li Battiati, ITALY;

Giuseppe Ferla, Catania, ITALY; Marco Camalleri, Palermo, ITALY;

\*\* CONTINUING DATA \*\*\*\*\*

\*\* FOREIGN APPLICATIONS \*\*\*\*\*

EUROPEAN PATENT OFFICE (EPO) 02425803.0 12/30/2002

IF REQUIRED, FOREIGN FILING LICENSE GRANTED

\*\* 04/29/2004

Foreign Priority claimed <input checked="" type="checkbox"/> yes <input type="checkbox"/> no	STATE OR	SHEETS	TOTAL	INDEPENDENT
35 USC 119 (a-d) conditions met <input checked="" type="checkbox"/> yes <input type="checkbox"/> no <input type="checkbox"/> Met after Allowance	COUNTRY	DRAWING	CLAIMS	CLAIMS
Verified and Acknowledged	ITALY	8	36	4
<i>Victor A. Pandala</i> Examiner's Signature	<i>VAMS</i> Initials			

## ADDRESS

27975

ALLEN, DYER, DOPPELT, MILBRATH &amp; GILCHRIST P.A.

1401 CITRUS CENTER 255 SOUTH ORANGE AVENUE

P.O. BOX 3791

ORLANDO, FL

32802-3791

## TITLE

Vertical-conduction and planar-structure MOS device with a double thickness of gate oxide and method for realizing power vertical MOS transistors with improved static and dynamic performances and high scaling down density

☐ All Fees☐ 1.16 Fees ( Filing )